Eric Tourni

List of Publications by Citations

271 papers	4,281 citations	34 h-index	47 g-index
300 ext. papers	4,774 ext. citations	2.9 avg, IF	5.24 L-index

#	Paper	IF	Citations
271	Effects of low temperature on the cold start gaseous emissions from light duty vehicles fuelled by ethanol-blended gasoline. *Applied Energy*, **2013**, 102, 44-54	10.7	121
270	On the origin of carrier localization in Ga1−xInxNyAs1−y/GaAs quantum wells. *Applied Physics Letters*, **2001**, 78, 1562-1564	3.4	121
269	. *IEEE Journal of Selected Topics in Quantum Electronics*, **2014**, 20, 394-404	3.8	85
268	Mechanisms affecting the photoluminescence spectra of GaInNAs after post-growth annealing. *Applied Physics Letters*, **2002**, 80, 4148-4150	3.4	79
267	Surfactant-mediated molecular beam epitaxy of strained layer semiconductor heterostructures. *Thin Solid Films*, **1993**, 231, 43-60	2.2	73
266	Continuous-wave operation above room temperature of GaSb-based laser diodes grown on Si. *Applied Physics Letters*, **2011**, 99, 121113	3.4	69
265	Nanoindentation of Si, GaP, GaAs and ZnSe single crystals. *Journal Physics D: Applied Physics*, **2003**, 36, L5-L9	3	59
264	GaSb-Based Laser, Monolithically Grown on Silicon Substrate, Emitting at 1.55 mu m at Room Temperature. *IEEE Photonics Technology Letters*, **2010**, 22, 553-555	2.2	58
263	Silicon-on-insulator spectrometers with integrated GaInAsSb photodiodes for wide-band spectroscopy from 1510 to 2300 nm. *Optics Express*, **2013**, 21, 6101-8	3.3	57
262	Annealing effects on the crystal structure of GaInNAs quantum wells with large In and N content grown by molecular beam epitaxy. *Journal of Applied Physics*, **2003**, 94, 2319-2324	2.5	56
261	Nanoscale analysis of the In and N spatial redistributions upon annealing of GaInNAs quantum wells. *Applied Physics Letters*, **2004**, 84, 2503-2505	3.4	54
260	Novel plastic strain-relaxation mode in highly mismatched III-V layers induced by two-dimensional epitaxial growth. *Applied Physics Letters*, **1995**, 66, 2265-2267	3.4	54
259	Silicon-based heterogeneous photonic integrated circuits for the mid-infrared. *Optical Materials Express*, **2013**, 3, 1523	2.6	52
258	Localized surface plasmon resonances in highly doped semiconductors nanostructures. *Applied Physics Letters*, **2012**, 101, 161113	3.4	48
257	Nature of the band gap in Zn1−xBexSe alloys. *Physical Review B*, **2000**, 61, 5332-5336	3.3	46
256	Structural and optical properties of Al0.48In0.52As layers grown on InP by molecular beam epitaxy: Influence of the substrate temperature and of a buffer layer. *Journal of Applied Physics*, **1991**, 70, 7362-7369	2.5	45
255	Interfacial intermixing in InAs/GaSb short-period-superlattices grown by molecular beam epitaxy. *Applied Physics Letters*, **2010**, 96, 021904	3.4	42

254	Study of evanescently-coupled and grating-assisted GaInAsSb photodiodes integrated on a silicon photonic chip. *Optics Express*, **2012**, 20, 11665-72	3.3	42
253	Interface analysis of InAs/GaSb superlattice grown by MBE. *Journal of Crystal Growth*, **2007**, 301-302, 889-892	1.6	42
252	Quantum cascade lasers grown on silicon. *Scientific Reports*, **2018**, 8, 7206	4.9	41
251	GaSbBi/GaSb quantum well laser diodes. *Applied Physics Letters*, **2017**, 110, 222106	3.4	40
250	Brewster "mode" in highly doped semiconductor layers: an all-optical technique to monitor doping concentration. *Optics Express*, **2014**, 22, 24294-303	3.3	38
249	Influence of alloy stability on the photoluminescence properties of GaAsN/GaAs quantum wells grown by molecular beam epitaxy. *Applied Physics Letters*, **2001**, 79, 3404-3406	3.4	38
248	GaInNAs/GaAs quantum wells grown by molecular-beam epitaxy emitting above 1.5 Îm. *Applied Physics Letters*, **2003**, 82, 1845-1847	3.4	37
247	Decomposition in as-grown (Ga,In)(N,As) quantum wells. *Applied Physics Letters*, **2005**, 87, 171901	3.4	37
246	Structural and optical characterization of ZnSe single crystals grown by solid-phase recrystallization. *Journal of Applied Physics*, **1996**, 80, 2983-2989	2.5	37
245	Photoluminescence of virtual-surfactant grown InAs/Al0.48In0.52As single quantum wells. *Applied Physics Letters*, **1992**, 60, 2877-2879	3.4	37
244	Metamorphic III–V semiconductor lasers grown on silicon. *MRS Bulletin*, **2016**, 41, 218-223	3.2	37
243	Online characterization of regulated and unregulated gaseous and particulate exhaust emissions from two-stroke mopeds: a chemometric approach. *Analytica Chimica Acta*, **2012**, 717, 28-38	6.6	36
242	Room-temperature operation of a 2.25 Îm electrically pumped laser fabricated on a silicon substrate. *Applied Physics Letters*, **2009**, 94, 061124	3.4	35
241	GaSb-based, 2.2 Îm type-I laser fabricated on GaAs substrate operating continuous wave at room temperature. *Applied Physics Letters*, **2009**, 94, 023506	3.4	35
240	Long wavelength GaInNAs/GaAs quantum-well heterostructures grown by solid-source molecular-beam epitaxy. *Applied Physics Letters*, **2000**, 77, 2189-2191	3.4	35
239	Surfactant-mediated molecular-beam epitaxy of III–V strained-layer heterostructures. *Journal of Crystal Growth*, **1995**, 150, 460-466	1.6	35
238	Photoluminescence study of ZnSe single crystals grown by solid-phase recrystallization. *Applied Physics Letters*, **1996**, 68, 1356-1358	3.4	35
237	Structural and optical properties of lattice-matched ZnBeSe layers grown by molecular-beam epitaxy onto GaAs substrates. *Applied Physics Letters*, **1997**, 70, 3564-3566	3.4	34

236	High temperature liquid phase epitaxy of (100) oriented GaInAsSb near the miscibility gap boundary. *Journal of Crystal Growth*, **1990**, 104, 683-694	1.6	34
235	Correlation between interface structure and light emission at 1.3–1.55 μm of (Ga,In)(N,As) diluted nitride heterostructures on GaAs substrates. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 2195		33
234	Vibrational evidence for a percolative behavior in Zn1−xBexSe. *Physical Review B*, **2001**, 65,	3.3	33
233	2.5 μm GaInAsSb lattice-matched to GaSb by liquid phase epitaxy. *Journal of Applied Physics*, **1990**, 68, 5936-5938	2.5	33
232	Molecular beam epitaxy and characterization of high Bi content GaSbBi alloys. *Journal of Crystal Growth*, **2017**, 477, 144-148	1.6	32
231	Hetero-epitaxial growth of BexZn1−xSe on Si(0 0 1) and GaAs(0 0 1) substrates. *Journal of Crystal Growth*, **1998**, 184-185, 11-15	1.6	32
230	From GaAs:N to oversaturated GaAsN: Analysis of the band-gap reduction. *Physical Review B*, **2004**, 69,	3.3	32
229	Interplay between the growth temperature, microstructure, and optical properties of GaInNAs quantum wells. *Applied Physics Letters*, **2003**, 82, 3451-3453	3.4	32
228	Mid-Infrared Semiconductor Lasers. *Semiconductors and Semimetals*, **2012**, 183-226	0.6	31
227	Correlations between structural and optical properties of GaInNAs quantum wells grown by MBE. *Journal of Crystal Growth*, **2003**, 251, 383-387	1.6	31
226	Spectroscopy of donor-acceptor pairs in nitrogen-doped ZnSe. *Physical Review B*, **1996**, 54, 4714-4721	3.3	31
225	Simulations of heteroepitaxial growth. *Journal of Crystal Growth*, **1997**, 178, 258-267	1.6	30
224	Evaluation of the potential of ZnSe and Zn(Mg)BeSe compounds for ultraviolet photodetection. *IEEE Journal of Quantum Electronics*, **2001**, 37, 1146-1152	2	30
223	Universal description of III-V/Si epitaxial growth processes. *Physical Review Materials*, **2018**, 2,	3.2	30
222	Room-temperature continuous-wave operation in the telecom wavelength range of GaSb-based lasers monolithically grown on Si. *APL Photonics*, **2017**, 2, 061301	5.2	30
221	Heterogeneous Integration of GaInAsSb p-i-n Photodiodes on a Silicon-on-Insulator Waveguide Circuit. *IEEE Photonics Technology Letters*, **2011**, 23, 1760-1762	2.2	28
220	Molecular-beam epitaxy of InSb/GaSb quantum dots. *Journal of Applied Physics*, **2007**, 101, 124309	2.5	28
219	Near-Field Thermophotovoltaic Conversion with High Electrical Power Density and Cell Efficiency above 14. *Nano Letters*, **2021**, 21, 4524-4529	11.5	28

218	X-ray diffraction study of GaSb grown by molecular beam epitaxy on silicon substrates. *Journal of Crystal Growth*, **2016**, 439, 33-39	1.6	27
217	Long-wave phonons in ZnSeBeSe mixed crystals: Raman scattering and percolation model. *Physical Review B*, **2004**, 70,	3.3	27
216	Growth limitations by the miscibility gap in liquid phase epitaxy of Ga1InxAsySb1 on GaSb. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1991**, 9, 125-128	3.1	26
215	InAs/Ga0.47In0.53As quantum wells: A new III-V materials system for light emission in the mid-infrared wavelength range. *Applied Physics Letters*, **1992**, 61, 2808-2810	3.4	26
214	Mid-infrared laser diodes epitaxially grown on on-axis (001) silicon. *Optica*, **2020**, 7, 263	8.6	26
213	Scattered light noise in gravitational wave interferometric detectors: A statistical approach. *Physical Review D*, **1997**, 56, 6085-6095	4.9	25
212	Virtual-surfactant epitaxy of strained InAs/Al0.48In0.52As quantum wells. *Applied Physics Letters*, **1993**, 62, 858-860	3.4	25
211	Interplay between Surface Stabilization, Growth Mode and Strain Relaxation during Molecular-Beam Epitaxy of Highly Mismatched III-V Semiconductor Layers. *Europhysics Letters*, **1994**, 25, 663-668	1.6	25
210	Mid-infrared GaSb-based EP-VCSEL emitting at 2.63 [micro sign]m. *Electronics Letters*, **2009**, 45, 265	1.1	24
209	Visible-blind ultraviolet photodetectors based on ZnMgBeSe Schottky barrier diodes. *Applied Physics Letters*, **2001**, 78, 4190-4192	3.4	24
208	Nanoindentation study of Zn1xBexSe heteroepitaxial layers. *Journal Physics D: Applied Physics*, **2002**, 35, 3015-3020	3	24
207	Raman study of ZnxBe1Se alloy (100) epitaxial layers. *Applied Physics Letters*, **2000**, 77, 519-521	3.4	24
206	Temperature dependence of the photoluminescence of Zn1CdxSe/ZnSe strained-layer quantum wells. *Applied Physics Letters*, **1995**, 67, 103-105	3.4	24
205	Surface stoichiometry, epitaxial morphology and strain relaxation during molecular beam epitaxy of highly strained InAs/Ga0.47In0.53As heterostructures. *Journal of Crystal Growth*, **1994**, 135, 97-112	1.6	24
204	GaInAsSb/GaSb pn photodiodes for detection to 2.4 m. *Electronics Letters*, **1991**, 27, 1237	1.1	24
203	Midwave infrared barrier detector based on Ga-free InAs/InAsSb type-II superlattice grown by molecular beam epitaxy on Si substrate. *Infrared Physics and Technology*, **2019**, 96, 39-43	2.7	24
202	High-density, uniform InSbGaSb quantum dots emitting in the midinfrared region. *Applied Physics Letters*, **2006**, 89, 263118	3.4	23
201	Highly doped semiconductor plasmonic nanoantenna arrays for polarization selective broadband surface-enhanced infrared absorption spectroscopy of vanillin. *Nanophotonics*, **2017**, 7, 507-516	6.3	22

200	Silicon surface preparation for III-V molecular beam epitaxy. *Journal of Crystal Growth*, **2015**, 413, 17-24	1.6	22
199	GaSb-based VCSELs emitting in the mid-infrared wavelength range (2 3 m) grown by MBE. *Journal of Crystal Growth*, **2009**, 311, 1912-1916	1.6	22
198	Zn(Mg)BeSe-based p-i-n photodiodes operating in the blue-violet and near-ultraviolet spectral range. *Applied Physics Letters*, **2000**, 76, 242-244	3.4	22
197	Defect control during growth of highly mismatched (100) InAsGaAs-heterostructures. *Journal of Crystal Growth*, **1995**, 146, 368-373	1.6	22
196	Growth mechanism of GaAs on (110) GaAs studied by high-energy electron diffraction and atomic force microscopy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1994**, 12, 2574		22
195	Silicon-on-insulator shortwave infrared wavelength meter with integrated photodiodes for on-chip laser monitoring. *Optics Express*, **2014**, 22, 27300-8	3.3	21
194	Interface properties of (Ga,In)(N,As) and (Ga,In)(As,Sb) materials systems grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2009**, 311, 1739-1744	1.6	21
193	Self-compensation in nitrogen-doped ZnSe. *Physical Review B*, **1997**, 56, R1657-R1660	3.3	21
192	Spectroscopy of the phosphorus impurity in ZnSe epitaxial layers grown by molecular-beam epitaxy. *Physical Review B*, **2000**, 61, 15789-15796	3.3	21
191	Liquid phase epitaxy and characterization of InAs1- x - ySb x P y on (100) InAs. *Journal of Crystal Growth*, **1992**, 121, 463-472	1.6	20
190	New III-V double-heterojunction laser emitting near 3.2 m. *Electronics Letters*, **1988**, 24, 1542	1.1	20
189	Subpicosecond timescale carrier dynamics in GaInAsSb AlGaAsSb double quantum wells emitting at 2.3 m. *Applied Physics Letters*, **2008**, 92, 101931	3.4	19
188	Single-mode monolithic GaSb Vertical-Cavity Surface-Emitting Laser. *Optics Express*, **2012**, 20, 15540-6	3.3	18
187	ZnSe-based Schottky barrier photodetectors. *Electronics Letters*, **2000**, 36, 352	1.1	18
186	Anti phase boundary free GaSb layer grown on 300 mm (001)-Si substrate by metal organic chemical vapor deposition. *Thin Solid Films*, **2018**, 645, 5-9	2.2	17
185	Defect density in ZnSe pseudomorphic layers grown by molecular beam epitaxy on to various GaAs buffer layers. *Journal of Crystal Growth*, **1998**, 192, 102-108	1.6	17
184	High-density InSb-based quantum dots emitting in the mid-infrared. *Journal of Crystal Growth*, **2007** , 301-302, 713-717	1.6	17
183	Percolation-based vibrational picture to estimate nonrandom N substitution in GaAsN alloys. *Applied Physics Letters*, **2003**, 82, 2808-2810	3.4	17

182	Evidence of N-related compensating donors in lightly doped ZnSe:N. *Applied Physics Letters*, **1999**, 74, 2200-2202	3.4	17
181	Analysis of epitaxial GaxIn1−xAs/InP and AlyIn1−yAs/InP interface region by high resolution x-ray diffraction. *Applied Physics Letters*, **1993**, 62, 149-151	3.4	17
180	Strained InAs single quantum wells embedded in a Ga0.47In0.53As matrix. *Applied Physics Letters*, **1992**, 61, 846-848	3.4	17
179	Micron-sized liquid nitrogen-cooled indium antimonide photovoltaic cell for near-field thermophotovoltaics. *Optics Express*, **2019**, 27, A11-A24	3.3	17
178	Localized surface plasmon resonance frequency tuning in highly doped InAsSb/GaSb one-dimensional nanostructures. *Nanotechnology*, **2016**, 27, 425201	3.4	16
177	Effect of nitrogen on the band structure and material gain of In/sub y/Ga/sub 1-y/As/sub 1-x/Nx-GaAs quantum wells. *IEEE Journal of Selected Topics in Quantum Electronics*, **2003**, 9, 716-722	3.8	15
176	Anisotropic misfit dislocation nucleation in two-dimensional grown InAs/GaAs(001) heterostructures. *Applied Physics Letters*, **1998**, 73, 1074-1076	3.4	15
175	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. *Applied Physics Letters*, **2018**, 112, 151905	3.4	14
174	Mid-infrared characterization of refractive indices and propagation losses in GaSb/AlXGa1−XAsSb waveguides. *Applied Physics Letters*, **2015**, 107, 171901	3.4	14
173	Isoelectronic traps in heavily doped GaAs:(In,N). *Physical Review B*, **2003**, 68,	3.3	14
172	Raman study of Zn1−xBexSe/GaAs systems with low Be content (x?0.20). *Journal of Applied Physics*, **2002**, 91, 9187-9197	2.5	14
171	p-type doping of Zn(Mg)BeSe epitaxial layers. *Applied Physics Letters*, **1999**, 75, 382-384	3.4	14
170	Zinc-blende group III-V/group IV epitaxy: Importance of the miscut. *Physical Review Materials*, **2020**, 4,	3.2	14
169	Type I GaSb1-xBix/GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. *Journal of Applied Physics*, **2019**, 125, 205706	2.5	13
168	Mid-IR GaSb-Based Bipolar Cascade VCSELs. *IEEE Photonics Technology Letters*, **2013**, 25, 882-884	2.2	13
167	Heteroepitaxial growth of BeSe on vicinal Si(001) surfaces. *Applied Physics Letters*, **1998**, 73, 957-959	3.4	13
166	Overlayer strain: A key to directly tune the topography of high-index semiconductor surfaces. *Applied Physics Letters*, **1993**, 63, 3300-3302	3.4	13
165	Influence of the Growth Mode on the Microstructure of Highly Mismatched InAs/GaAs Heterostructures. *Physica Status Solidi A*, **1994**, 145, 481-489		13

164	Virtual-surfactant-induced wetting in strained-layer heteroepitaxy. *Applied Physics A: Solids and Surfaces*, **1993**, 56, 91-94		13
163	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. *Physical Review B*, **2018**, 97,	3.3	13
162	InAs-based quantum cascade lasers grown on on-axis (001) silicon substrate. *APL Photonics*, **2020**, 5, 041302	5.2	12
161	Optical performances of InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission. *Journal of Applied Physics*, **2010**, 108, 093107	2.5	12
160	New results on the solid-phase recrystallisation of ZnSe. *Journal of Crystal Growth*, **1998**, 184-185, 1021-1025	1.6	12
159	InAs/GaSb short-period superlattice injection lasers operating in 2.5 [micro sign]m–3.5 [micro sign]m mid-infrared wavelength range. *Electronics Letters*, **2007**, 43, 1285	1.1	12
158	Molecular-beam epitaxy of high-quality ZnSe homo-epitaxial layers on solid-phase recrystallized substrates. *Applied Physics Letters*, **1996**, 69, 3221-3223	3.4	12
157	Virtual-surfactant epitaxy of InAs quantum wells. *Journal of Crystal Growth*, **1993**, 127, 765-769	1.6	12
156	Indium antimonide photovoltaic cells for near-field thermophotovoltaics. *Solar Energy Materials and Solar Cells*, **2019**, 203, 110190	6.4	11
155	Low-loss orientation-patterned GaSb waveguides for mid-infrared parametric conversion. *Optical Materials Express*, **2017**, 7, 3011	2.6	11
154	GaSb-based composite quantum wells for laser diodes operating in the telecom wavelength range near 1.55-μm. *Applied Physics Letters*, **2015**, 106, 101102	3.4	11
153	Highly tensile-strained, type-II, Ga1−xInxAs/GaSb quantum wells. *Applied Physics Letters*, **2010**, 96, 062109	3.4	11
152	Modelling of an InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission by the k.p method. *Journal Physics D: Applied Physics*, **2010**, 43, 325102	3	11
151	InAs/GaSb/InSb short-period super-lattice diode lasers emitting near 3.3 [micro sign]m at room-temperature. *Electronics Letters*, **2009**, 45, 165	1.1	11
150	(001) GaAs substrate preparation for direct ZnSe heteroepitaxy. *Journal of Applied Physics*, **1997**, 81, 7012-7017	2.5	11
149	Electronic structure and radiative lifetimes of ideal Zn1−xBexSe alloys. *Solid State Communications*, **2002**, 123, 209-212	1.6	11
148	Photoluminescence spectroscopy of Ga(In)NAs quantum wells for emission at 1.5 μm. *Solid-State Electronics*, **2003**, 47, 477-482	1.7	11
147	Molecular-beam epitaxy of BeTe layers on GaAs substrates studied via reflection high-energy electron diffraction. *Applied Physics Letters*, **1998**, 72, 2859-2861	3.4	11

146	Ohmic contacts to p-type ZnSe using a ZnSe/BeTe superlattice. *Applied Physics Letters*, **1999**, 75, 3345-3347	3.4	11
145	New developments in the heteroepitaxial growth of Be-chalcogenides based semiconducting alloys. *Journal of Electronic Materials*, **1999**, 28, 662-665	1.9	11
144	Structural characterization of lattice matched AlxIn1−xAs/InP and GayIn1−yAs/InP heterostructures by transmission electron microscopy and high-resolution x-ray diffraction. *Journal of Applied Physics*, **1995**, 78, 2403-2410	2.5	11
143	Long-wavelength strained-layer InAs/GaInAs single-quantum-well laser grown by molecular beam epitaxy on InP substrate. *Electronics Letters*, **1993**, 29, 1255	1.1	11
142	Characteristic temperature Toof Ga0.83In0.17As0.15Sb0.85/AI0.27Ga0.73As0.02Sb0.98 injection lasers. *Electronics Letters*, **1988**, 24, 1076	1.1	11
141	A Stress-Free and Textured GaP Template on Silicon for Solar Water Splitting. *Advanced Functional Materials*, **2018**, 28, 1801585	15.6	11
140	Characterization of antimonide based material grown by molecular epitaxy on vicinal silicon substrates via a low temperature AlSb nucleation layer. *Journal of Crystal Growth*, **2017**, 477, 65-71	1.6	10
139	Issues in molecular-beam epitaxy of ZnSe-based heterostructures for blue-green lasers. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1997**, 43, 21-28	3.1	10
138	The phosphorus acceptor in ZnSe. *Journal of Crystal Growth*, **1998**, 184-185, 515-519	1.6	10
137	Does In-bonding delay GaN-segregation in GaInAsN? A Raman study. *Applied Physics Letters*, **2004**, 85, 5872-5874	3.4	10
136	Molecular beam epitaxial growth and characterization of Be(Zn)Se on Si(0 0 1) and GaAs(0 0 1). *Journal of Crystal Growth*, **2000**, 214-215, 95-99	1.6	10
135	Selective growth of ordered hexagonal InN nanorods. *CrystEngComm*, **2019**, 21, 2702-2708	3.3	9
134	Recombination channels in 2.4–3.2 μm GaInAsSb quantum-well lasers. *Semiconductor Science and Technology*, **2013**, 28, 015015	1.8	9
133	Surface-enhanced infrared absorption with Si-doped InAsSb/GaSb nano-antennas. *Optics Express*, **2017**, 25, 26651-26661	3.3	9
132	Type II transition in InSb-based nanostructures for midinfrared applications. *Journal of Applied Physics*, **2008**, 103, 114516	2.5	9
131	MBE growth and interface formation of compound semiconductor heterostructures for optoelectronics. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 2683-2696	1.3	9
130	Current Activity in CNRS-Sophia Antipolis Regarding Wide-Gap II–VI Materials. *Physica Status Solidi (B): Basic Research*, **1995**, 187, 457-466	1.3	9
129	Optical properties of InAs quantum wells emitting between 0.9 mu m and 2.5 mu m. *Semiconductor Science and Technology*, **1993**, 8, S236-S239	1.8	9

128	Interface energy analysis of III□V islands on Si (001) in the Volmer-Weber growth mode. *Applied Physics Letters*, **2018**, 113, 191601	3.4	9
127	Fano-like resonances sustained by Si doped InAsSb plasmonic resonators integrated in GaSb matrix. *Optics Express*, **2015**, 23, 29423-33	3.3	8
126	Selective lateral etching of InAs/GaSb tunnel junctions for mid-infrared photonics. *Semiconductor Science and Technology*, **2012**, 27, 085011	1.8	8
125	Non-random Be-to-Zn substitution in ZnBeSe alloys: Raman scattering and ab initio calculations. *European Physical Journal B*, **2010**, 73, 461-469	1.2	8
124	New results and trends in the solid phase recrystallization of ZnSe. *Materials Letters*, **1998**, 36, 162-166	3.3	8
123	Conduction-band crossover induced by misfit strain in InSb□GaSb self-assembled quantum dots. *Physical Review B*, **2007**, 76,	3.3	8
122	Structural and optical properties of InSb quantum dots for mid-IR applications. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 3959-3962	1.3	8
121	Wide-band-gap ZnMgBeSe alloys grown onto GaAs by molecular beam epitaxy. *Journal of Crystal Growth*, **2001**, 223, 461-465	1.6	8
120	Direct evidence for the trigonal symmetry of shallow phosphorus acceptors in ZnSe. *Physical Review B*, **2001**, 64,	3.3	8
119	Tunable generation of nanometer-scale corrugations on high-index III-V semiconductor surfaces. *Physical Review B*, **1994**, 49, 11053-11059	3.3	8
118	Growth by liquid phase epitaxy and characterization of GaInAsSb and InAsSbP alloys for mid-infrared applications (2-3 um) **1991**,		8
117	Phosphonate monolayers on InAsSb and GaSb surfaces for mid-IR plasmonics. *Applied Surface Science*, **2018**, 451, 241-249	6.7	8
116	Electron tomography on III-Sb heterostructures on vicinal Si(001) substrates: Anti-phase boundaries as a sink for threading dislocations. *Scripta Materialia*, **2017**, 132, 5-8	5.6	7
115	Growth and characterization of AlInAsSb layers lattice-matched to GaSb. *Journal of Crystal Growth*, **2017**, 477, 72-76	1.6	7
114	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. *Acta Materialia*, **2018**, 143, 121-129	8.4	7
113	Dominant carrier recombination mechanisms in GaInNAs□GaAs quantum well light-emitting diodes. *Applied Physics Letters*, **2004**, 85, 40-42	3.4	7
112	Bi-modal Raman response of Be□Se vibration in Zn1□□MgyBexSe alloys. *Journal of Alloys and Compounds*, **2004**, 382, 271-274	5.7	7
111	Native vacancies in nitrogen-doped and undoped ZnSe layers studied by positron annihilation. *Physical Review B*, **2000**, 62, 15711-15717	3.3	7

110	Study of the band alignment in (Zn, Cd)Se/ZnSe quantum wells by means of photoluminescence excitation spectroscopy. *Journal of Applied Physics*, **2000**, 87, 1863-1868	2.5	7
109	Strained InAs/Ga0.47In0.53As quantum-well heterostructures grown by molecular-beam epitaxy for long-wavelength laser applications. *Solid-State Electronics*, **1994**, 37, 1311-1314	1.7	7
108	Structural properties and transport characteristics of pseudomorphic GaxIn1−xAs/AlyIn1−yAs modulation-doped heterostructures grown by molecular-beam epitaxy. *Journal of Applied Physics*, **1992**, 71, 1790-1797	2.5	7
107	In situ determination of the growth conditions of GaSbBi alloys. *Journal of Crystal Growth*, **2018**, 495, 9-13	1.6	7
106	Massless Dirac fermions in III-V semiconductor quantum wells. *Physical Review B*, **2019**, 99,	3.3	6
105	Atomic structure of tensile-strained GaAs/GaSb(001) nanostructures. *Applied Physics Letters*, **2013**, 102, 102105	3.4	6
104	ZnSe homoepitaxial growth on solid-phase recrystallized substrates. *Journal of Crystal Growth*, **1997**, 175-176, 577-582	1.6	6
103	The nitrogen-related shallow donor in ZnSe : N epitaxial layers. *Journal of Crystal Growth*, **1998**, 184-185, 520-524	1.6	6
102	Vibrational Evidence for Percolative Behavior in ZnBeSe. *Physica Status Solidi (B): Basic Research*, **2002**, 229, 25-29	1.3	6
101	Double period RHEED oscillations during MBE growth of GaAs and AlAs on the GaAs(110) surface. *Surface Science*, **1995**, 331-333, 479-484	1.8	6
100	Interband cascade Lasers with AlGaAsSb cladding layers emitting at 3.3 μm. *Optics Express*, **2019**, 27, 31425-31434	3.3	6
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